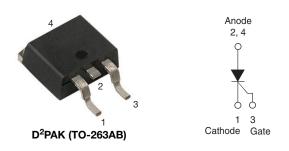


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Vishay Semiconductors

Thyristor Surface Mount, Phase Control SCR, 8 A



PRIMARY CHARACTERISTICS							
I _{T(AV)} 8 A							
V_{DRM}/V_{RRM}	800 V						
V_{TM}	1.2 V						
I _{GT}	15 mA						
T_J	-40 to +125 °C						
Package	D ² PAK (TO-263AB)						
Circuit configuration	Single SCR						

FEATURES

 Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



- AEC-Q101 qualified
- Meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- · On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

DESCRIPTION

The VS-12TTS08SLHM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS								
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	13.5	17	А					

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	TEST CONDITIONS	VALUES	UNITS					
I _{T(AV)}	Sinusoidal waveform	8	^					
I _{T(RMS)}		12.5	A					
V_{RRM}/V_{DRM}		800	V					
I _{TSM}		110	А					
V _T	8 A, T _J = 25 °C	1.2	V					
dV/dt		150	V/µs					
dl/dt		100	A/µs					
T _J	Range	-40 to +125	°C					

VOLTAGE RATINGS										
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} / I _{DRM} AT 125 °C mA							
VS-12TTS08SLHM3	800	800	5.0							



ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum average on-state current	I _{T(AV)}	T = 100 °C 190° conduction half sine ways	8	А				
Maximum RMS on-state current	I _{T(RMS)}	T _C = 108 °C, 180° conduction, half sine wave	12.5					
Maximum peak one-cycle	1	10 ms sine pulse, rated V _{RRM} applied, T _J = 125 °C	95					
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied, T _J = 125 °C	110					
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated V_{RRM} applied, T_J = 125 °C	45	A ² s				
Maximum i-t for fusing	I-t	10 ms sine pulse, no voltage reapplied, T _J = 125 °C	64					
Maximum I ² √t for fusing	I ² √t	$t = 0.1$ ms to 10 ms, no voltage reapplied, $T_J = 125$ °C	640	A²√s				
Maximum on-state voltage drop	V_{TM}	8 A, T _J = 25 °C	1.2	V				
On-state slope resistance	r _t	T _{.1} = 125 °C	16.2	mΩ				
Threshold voltage	V _{T(TO)}	1j = 123 0	0.87	V				
Maximum reverse and direct leakage current	1/1	$T_J = 25 ^{\circ}\text{C}$	0.05					
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	$V_R = \text{rated } V_{RRM} / V_{DRM}$	5.0					
Typical holding current I _H		Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C	30	mA				
Typical latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C	50					
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 \text{ %, } V_{DRM} = R_g - k = \text{open}$	150	V/µs				
Maximum rate of rise of turned-on current	dI/dt		100	A/µs				

TRIGGERING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak gate power	P_{GM}		8.0	W				
Maximum average gate power	$P_{G(AV)}$		2.0	VV				
Maximum peak positive gate current	+I _{GM}		1.5	Α				
Maximum peak negative gate voltage	-V _{GM}		10	V				
		Anode supply = 6 V, resistive load, T_J = - 65 °C	20					
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	15	mA				
		Anode supply = 6 V, resistive load, T _J = 125 °C	10					
		Anode supply = 6 V, resistive load, T _J = -65 °C	1.2					
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	1	v				
		Anode supply = 6 V, resistive load, T _J = 125 °C	0.7	V				
Maximum DC gate voltage not to trigger	V_{GD}	T = 105 °C V = reted value	0.2					
Maximum DC gate current not to trigger	I _{GD}	$T_J = 125$ °C, $V_{DRM} = rated value$	0.1	mA				

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t _{gt}	T _J = 25 °C	0.8					
Typical reverse recovery time	t _{rr}	T _{.I} = 125 °C	3	μs				
Typical turn-off time	t _q	1J = 125 O	100					



THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C				
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.5					
Maximum thermal resistance, junction to ambient	R _{thJA}		62	°C/W				
Typical thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, and greased	0.5					
Approximate weight			2	g				
Approximate weight			0.07	oz.				
Marking device		Case style D ² PAK (TO-263AB)	12TTS	08SH				

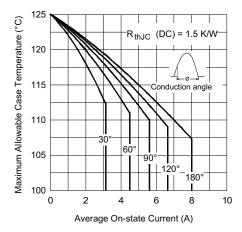


Fig. 1 - Current Rating Characteristics

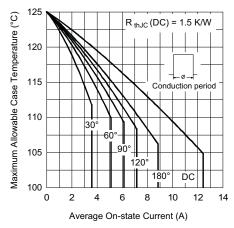


Fig. 2 - Current Rating Characteristics

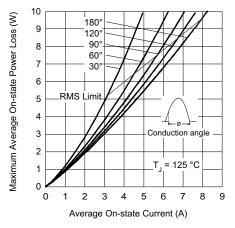


Fig. 3 - On-State Power Loss Characteristics

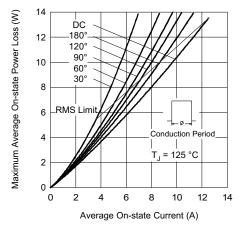


Fig. 4 - On-State Power Loss Characteristics

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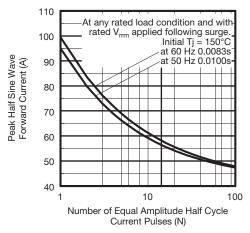


Fig. 5 - Maximum Non-Repetitive Surge Current

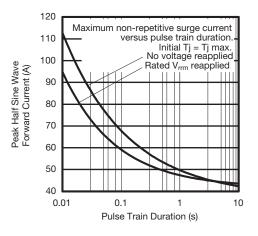


Fig. 6 - Maximum Non-Repetitive Surge Current

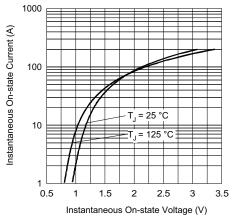


Fig. 7 - On-State Voltage Drop Characteristics

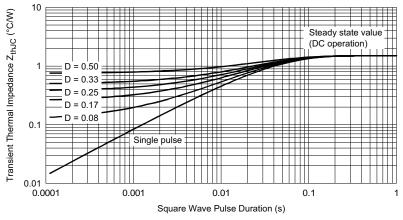
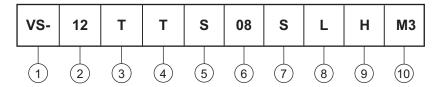


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics



ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- Current rating (12.5 A)
- Circuit configuration:

T = single thyristor

4 - Package:

 $T = D^2PAK (TO-263AB)$

5 - Type of silicon:

S = standard recovery rectifier

- 6 Voltage rating (08 = 800 V)
- 7 S = surface mountable
- 8 L = tape and reel (left oriented), for different orientation contact factory
- 9 H = AEC-Q101 qualified
- |10| Environmental digit:

M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-12TTS08SLHM3	800	800	13" diameter reel				

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95046</u>					
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96317				



D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	INCHES		NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



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